IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	Andrew R. Barow and Elizabeth Ann Whitsitt	§	ART UNIT:
SERIAL NO.:	10/535,358	§	EXAMINER:
FILED:		§	
FOR:	Method for Low Temperature Growth of Inorganic Materials From Solution Using Catalyzed Growth And Re-Growth	§	CONFIRMATION NO.:

INFORMATION DISCLOSURE STATEMENT

Atty. Dkt. No.: 1789-09405 CWS
Clt. Ref. No.: 21050
Date: January 11, 2006

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

This Information Disclosure Statement, including completed Form PTO-1449, comprises a list of pertinent art of which Applicants are aware.

The submission of this Information Disclosure Statement and the references submitted therewith is not an admission that the art cited is "prior" with respect to the present invention, nor is it a representation, that no better art exists. Applicants hereby reserve the right to swear behind or otherwise disprove any alleged "prior" nature of any art cited should the facts support and the situation warrant such an action. It is submitted that the art cited does not constitute a bar to the patentability of Applicants' invention under 35 U.S.C. § 102 or § 103.

No Office Action on the merits has been received in the present application, and Applicant believes that no fee is due. In the event that an Office Action dated prior to the mailing date of this Information Disclosure Statement has been issued, please charge Deposit

Account 03-2769, Conley Rose, P.C., in the amount of $180, so that this Information Disclosure Statement may be considered under Rule 1.97(c).

Respectfully submitted,

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PTO/SB/08a 07-05)
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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	1

Complete if Known	
Application Number	10/535,358
Filing Date	
First Named Inventor	Andrew R. Barron
Group Art Unit	
Examiner Name	
Attorney Docket Number	1789-09405 (21050) CWS

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (*if known*)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-6,080,683	06/27/2000		
	AB	US-5,073,408	12/17/1991		
	AC	US-5,132,140	07/21/1992		
	AD	US-5,616,233	04/01/1997		
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	AF	US-4,693,916	09/15/1987		
	AG	US-4,431,683	02/14/1984		
	AH	US-2,505,629	04/25/1950		

FOREIGN PATENT DOCUMENTS

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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate) title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issued number(s), publisher, city and/or country where published.	T[2]
	A1	"The Initial Growth Mechanism of Silicon Oxide by Liquid-Phase Deposition", Chou, J.-S. and Lee, S.-C., J. Electrochem. Soc., vol. 140, No. 11, Nov. 1994, pp. 3214-3218.	
	AJ	"A Selective SiO_2 Film-Formation Technology Using Liquid-Phase Deposition for Fully Planarized Multilevel Interconnections", Hommo, T., Katoh, T., Yamada, Y., and Murao, Y., J. Electrochem. Soc., vol. 140, No. 8, Aug. 1993, pp. 2410-2414.	
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	AN	"Characterization of Silica on Surface Preparation Processes for Advanced Gate Dielectrics", Okorn-Schmidt, H. F., IBM J. Res. Develop., vol. 43, No. 3, May 1999, pp. 351-365.	

Examiner Signature		Dated Considered	